

74HC1G86; 74HCT1G86

2-input EXCLUSIVE-OR gate

Rev. 04 — 20 July 2007

Product data sheet

1. General description

74HC1G86 and 74HCT1G86 are high-speed Si-gate CMOS devices. They provide a 2-input EXCLUSIVE-OR function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC/HCT86.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options
- Specified from –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

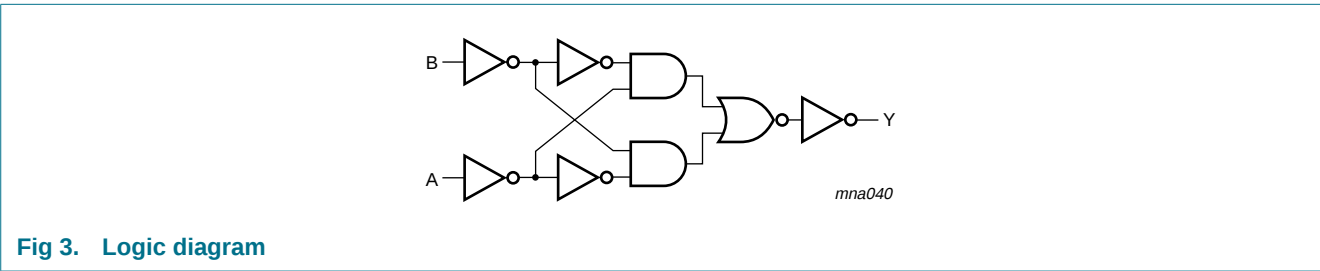
Type number	Package			
	Temperature range	Name	Description	Version
74HC1G86GW 74HCT1G86GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74HC1G86GV 74HCT1G86GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753

4. Marking

Table 2. Marking codes

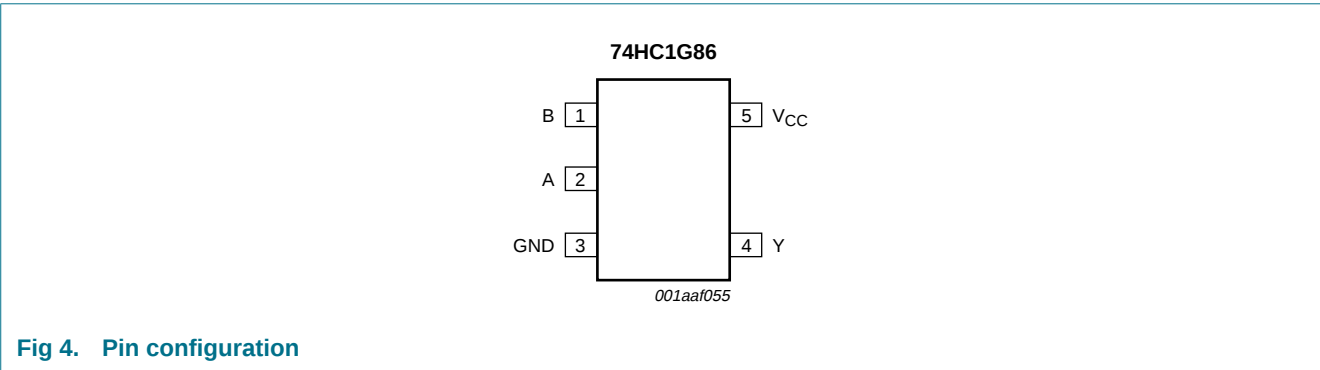
Type number	Marking
74HC1G86GW	HH
74HCT1G86GW	TH
74HC1G86GV	H86
74HCT1G86GV	T86

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description		
Symbol	Pin	Description
B	1	data input
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V _{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Inputs		Output
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [\[1\]](#)

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	-	±20	mA
I _O	output current	-0.5 V < V _O < V _{CC} + 0.5 V	-	±12.5	mA
I _{CC}	supply current		-	25	mA
I _{GND}	ground current		-25	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[2] -	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1G86			74HCT1G86			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	-	139	-	-	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
For type 74HC1G86								
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = −20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	V
		I _O = −20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	V
		I _O = −20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	V
		I _O = −2.0 mA; V _{CC} = 4.5 V	4.13	4.32	-	3.7	-	V
		I _O = −2.6 mA; V _{CC} = 6.0 V	5.63	5.81	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	V
		I _O = 2.0 mA; V _{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
		I _O = 2.6 mA; V _{CC} = 6.0 V	-	0.16	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	1.0	-	1.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	10	-	20	μA
C _I	input capacitance		-	1.5	-	-	-	pF
For type 74HCT1G86								
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = −20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	V
		I _O = −2.0 mA; V _{CC} = 4.5 V	4.13	4.32	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	V
		I _O = 2.0 mA; V _{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	1.0	-	1.0	μA

Table 7. Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$; $V_{CC} = 5.5\text{ V}$	-	-	10	-	20	μA
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5\text{ V}$ to 5.5 V ; $V_I = V_{CC} - 2.1\text{ V}$; $I_O = 0\text{ A}$	-	-	500	-	850	μA
C_I	input capacitance		-	1.5	-	-	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

$GND = 0\text{ V}$; $t_r = t_f \leq 6.0\text{ ns}$; All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$. For test circuit see [Figure 6](#)

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	

For type 74HC1G86

t_{pd}	propagation delay	A and B to Y; see Figure 5	[1]					
		$V_{CC} = 2.0\text{ V}$; $C_L = 50\text{ pF}$	-	22	115	-	135	ns
		$V_{CC} = 4.5\text{ V}$; $C_L = 50\text{ pF}$	-	11	23	-	27	ns
		$V_{CC} = 5.0\text{ V}$; $C_L = 15\text{ pF}$	-	9	-	-	-	ns
		$V_{CC} = 6.0\text{ V}$; $C_L = 50\text{ pF}$	-	9	20	-	23	ns
C_{PD}	power dissipation capacitance	$V_I = GND$ to V_{CC}	[2]					
			-	23	-	-	-	pF

For type 74HCT1G86

t_{pd}	propagation delay	A and B to Y; see Figure 5	[1]					
		$V_{CC} = 4.5\text{ V}$; $C_L = 50\text{ pF}$	-	13	23	-	27	ns
		$V_{CC} = 5.0\text{ V}$; $C_L = 15\text{ pF}$	-	10	-	-	-	ns
C_{PD}	power dissipation capacitance	$V_I = GND$ to $V_{CC} - 1.5\text{ V}$	[2]					
			-	23	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz

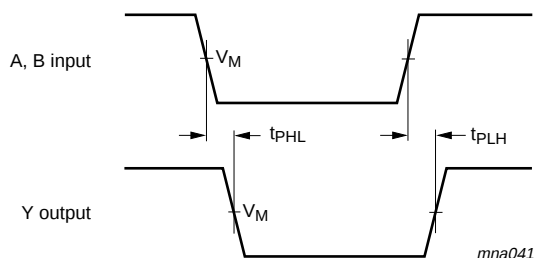
f_o = output frequency in MHz

C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

$\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs

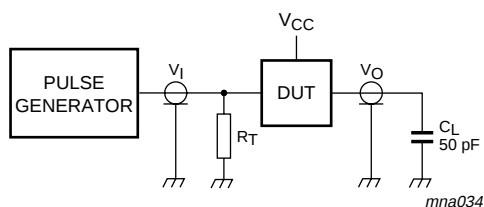
12. Waveforms



For 74HC1G86: $V_M = 0.5 \times V_{CC}$; $V_L = \text{GND to } V_{CC}$.

For 74HCT1G86: $V_M = 1.3 \text{ V}$; $V_L = \text{GND to } 3.0 \text{ V}$.

Fig 5. The input (A and B) to output (Y) propagation delays



Test data is given in [Table 8](#). Definitions for test circuit:

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 6. Load circuitry for switching times

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mmSOT353-1

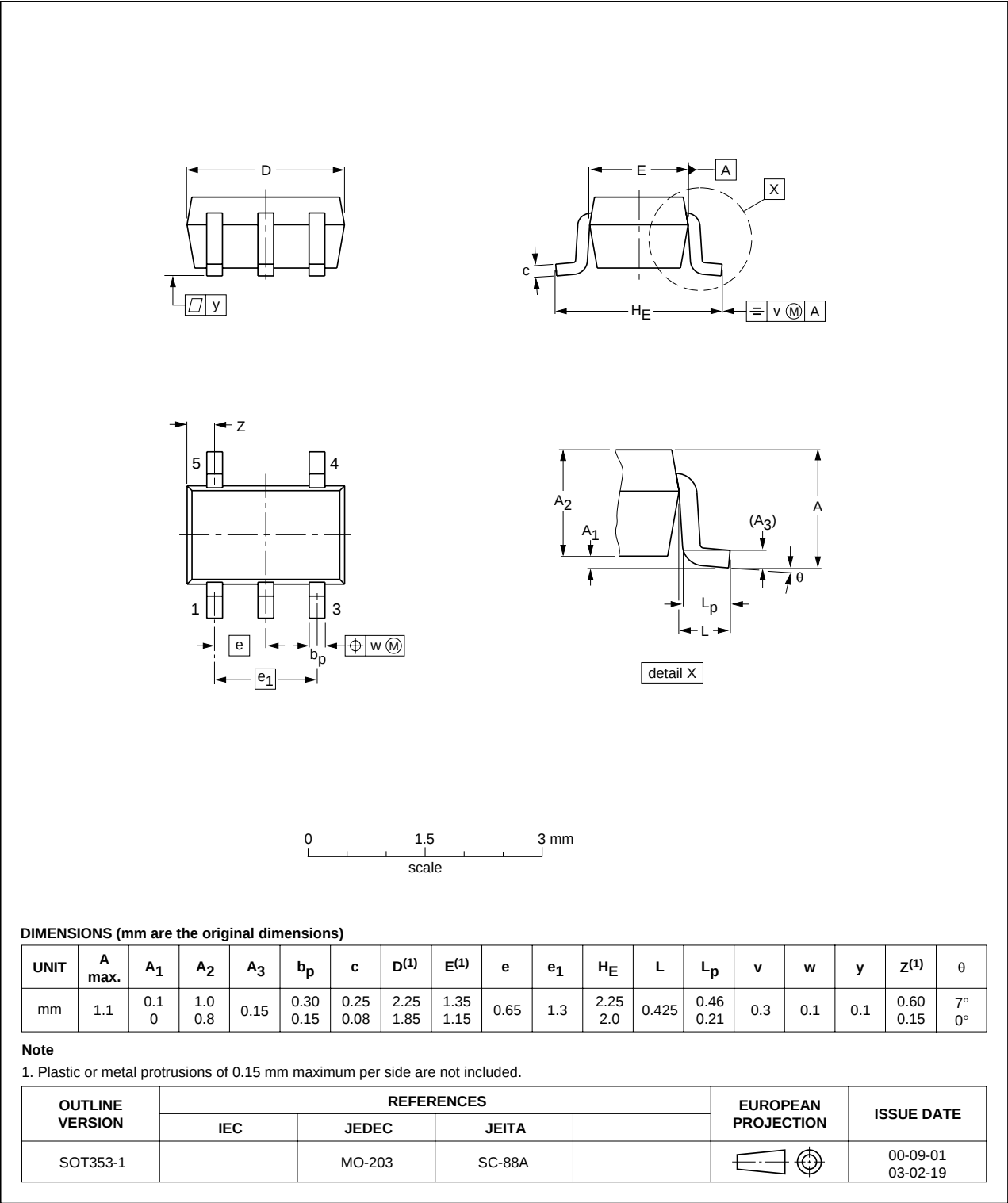


Fig 7. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753



Fig 8. Package outline SOT753 (SC-74A)

14. Abbreviations

Table 9. Abbreviations

Acronym	Description
DUT	Device Under Test
TTL	Transistor-Transistor Logic

15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G86_4	20070720	Product data sheet	-	74HC_HCT1G86_3
Modifications:	- The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. - Legal texts have been adapted to the new company name where appropriate. - Package SOT353 changed to SOT353-1 in Table 1 and Figure 7. - Quick Reference Data and Soldering sections removed. Section 2 "Features" updated.			
74HC_HCT1G86_3	20020515	Product specification	-	74HC_HCT1G86_2
74HC_HCT1G86_2	20010406	Product specification	-	74HC_HCT1G86_1
74HC_HCT1G86_1	19980805	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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